

Data Sheet Issue:- P2

## Phase Control Thyristor Types N0465WN140 to N0465WN160

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V <sub>DRM</sub>	Repetitive peak off-state voltage, (note 1)	1400-1600	V
V <sub>DSM</sub>	Non-repetitive peak off-state voltage, (note 1)	1500-1700	V
V <sub>RRM</sub>	Repetitive peak reverse voltage, (note 1)	1400-1600	V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage, (note 1)	1500-1700	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS		
I <sub>T(AV)M</sub>	Maximum average on-state current, T <sub>sink</sub> =55°C, (n	465	А		
I <sub>T(AV)M</sub>	Maximum average on-state current. T <sub>sink</sub> =85°C, (n	315	А		
I <sub>T(AV)M</sub>	Maximum average on-state current. T <sub>sink</sub> =85°C, (n	180	А		
I <sub>T(RMS)M</sub>	Nominal RMS on-state current, T <sub>sink</sub> =25°C, (note 2	920	А		
I <sub>T(d.c.)</sub>	D.C. on-state current, T <sub>sink</sub> =25°C, (note 4)	790	А		
I <sub>TSM</sub>	Peak non-repetitive surge $t_p=10ms$ , $V_{rm}=60\% V_{RRM}$	4500	А		
I <sub>TSM2</sub>	Peak non-repetitive surge $t_p=10ms$ , $V_{rm}\leq 10V$ , (not	5000	А		
l <sup>2</sup> t	$I^{2}t$ capacity for fusing t <sub>p</sub> =10ms, V <sub>rm</sub> =60%V <sub>RRM</sub> , (no	101×10 <sup>3</sup>	A <sup>2</sup> s		
l <sup>2</sup> t	$I^{2}t$ capacity for fusing t <sub>p</sub> =10ms, V <sub>m</sub> ≤10V, (note 5)	125×10 <sup>3</sup>	A <sup>2</sup> s		
		(continuous, 50Hz)	75	A/µs	
(di/dt) <sub>cr</sub>	Critical rate of rise of on-state current (note 6)	(repetitive, 50Hz, 60s)	125		
		(non-repetitive)	250		
V <sub>RGM</sub>	Peak reverse gate voltage	5	V		
P <sub>G(AV)</sub>	Mean forward gate power	3	W		
P <sub>GM</sub>	Peak forward gate power	30	W		
T <sub>j op</sub>	Operating temperature range	-60 to +125	°C		
T <sub>stg</sub>	Storage temperature range	-60 to +125	°C		

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T<sub>i</sub> below 25°C.

2) Double side cooled, single phase; 50Hz, 180° half-sinewave.

3) Anode side cooled, single phase; 50Hz, 180° half-sinewave.

4) Double side cooled.

5) Half-sinewave,  $125^{\circ}C T_{j}$  initial.

6)  $V_D=67\% V_{DRM}$ ,  $I_{TM}=600Å$ ,  $I_{FG}=2A$ ,  $t_r \le 0.5 \mu s$ ,  $T_{case}=125^{\circ}C$ .



## **Characteristics**

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V <sub>TM</sub>	Maximum peak on-state voltage	-	-	1.30	I <sub>TM</sub> =465A	V
V <sub>T0</sub>	Threshold voltage	-	-	0.90		V
r <sub>T</sub>	Slope resistance	-	-	0.85		mΩ
(dv/dt) <sub>cr</sub>	Critical rate of rise of off-state voltage	1000	-	-	$V_D$ =67% $V_{DRM}$ , linear ramp, gate o/c	V/µs
I <sub>DRM</sub>	Peak off-state current	-	-	50	Rated V <sub>DRM</sub>	mA
I <sub>RRM</sub>	Peak reverse current	-	-	50	Rated V <sub>RRM</sub>	mA
V <sub>GT</sub>	Gate trigger voltage	-	-	2.50		V
I <sub>GT</sub>	Gate trigger current	-	-	250	$T_j=25^{\circ}C$ $V_D=10V, I_T=3A$	mA
$V_{GD}$	Gate non-trigger voltage	-	-	0.25	Rated V <sub>DRM</sub>	V
I <sub>H</sub>	Holding current	-	-	250	T <sub>j</sub> =25°C	mA
t <sub>gd</sub>	Gate-controlled turn-on delay time	-	-	2.0	V <sub>D</sub> =67% V <sub>DRM</sub> , I <sub>T</sub> =300A, di/dt=10A/µs, I <sub>FG</sub> =2A, t <sub>i</sub> =0.5µs, T <sub>i</sub> =25°C	μs
t <sub>q</sub>	Turn-off time	-	-	125	I <sub>TM</sub> =300A, t <sub>p</sub> =500μs, di/dt=10A/μs, V <sub>r</sub> =100V, V <sub>dr</sub> =67%V <sub>DRM</sub> , dV <sub>dr</sub> /dt=50V/μs	μs
		-	-	0.080	Double side cooled	K/W
R <sub>thJK</sub>	Thermal resistance, junction to heatsink	-	-	0.174	Anode side cooled	K/W
		-	-	0.146	Cathode side cooled	K/W
F	Mounting force	5	-	7	Note 2.	kN
W <sub>t</sub>	Weight	-	70	-		g

Notes:-

1) Unless otherwise indicated  $T_j=125^{\circ}C$ .

2) For other clamp forces, please consult factory.



## **Outline Drawing & Ordering Information**

